

ABSTRACT OF THE DISCLOSURE

The semiconductor device comprises an interconnection buried in an interconnection groove formed in a lower insulating film, and an upper insulating film having a contact hole formed down to an end part of the interconnection. The interconnection groove is formed by using a design pattern having a main interconnection portion 100 and an extended portion 104 provided at an end part of a main interconnection portion 100 for forming the interconnection and extended perpendicularly to an extending direction of the main interconnection portion 100.